

DOCKET NO. 00-643/1D  
Preliminary Amendment  
August 29, 2003

Express Mailing Label No. ET532833503US

2003; and Serial [[No.]] [[Nos.]] 09/425,552; 09/346,493; 09/426,056; 09/426,061; 09/605,380; 09/607,512; 09/704,164; 09/704,200; all assigned to the assignee of this invention.

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-35 (Cancelled).

36. (Original) A low dielectric constant fluorine and carbon-doped silicon oxide dielectric material for use in an integrated circuit structure comprising: silicon atoms bonded to oxygen atoms; silicon atoms bonded to carbon atoms; and carbon atoms bonded to fluorine atoms; wherein said dielectric material also has a characteristic selected from the group consisting of:

- (a) the presence of at least one C-C bond;
- (b) the presence of at least one carbon atom bonded to from 1 to 2 fluorine atoms; and
- (c) the presence of at least one silicon atom bonded to from 0 to 2 oxygen atoms.

37. (Original) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 36 wherein said characteristic is the presence of at least one C-C bond, and at least one of the carbon atoms participating in said C-C bond is also bonded to at least one fluorine atom.

38. (Original) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 36 wherein all silicon atoms are bonded to at least 1 oxygen atom.

39. (Original) A low dielectric constant fluorine and carbon-doped silicon oxide dielectric material for use in an integrated circuit structure comprising the reaction product of an oxidizing agent and one or more silanes comprising one or more organofluoro silanes having the formula  $\text{SiR}_1\text{R}_2\text{R}_3\text{R}_4$ , wherein:

- 5           (a)  $\text{R}_1$  is selected from the group consisting of H, a 3 to 5 carbon organo moiety, and an oxyorgano moiety;
- (b)  $\text{R}_2$  is an organofluoro moiety; and
- (c)  $\text{R}_3$  and  $\text{R}_4$  are independently selected from the group consisting of the same or different leaving group, the same or different organofluoro moiety, and the same or different
- 10            $((\text{L})\text{Si}(\text{R}_5)(\text{R}_6))_n(\text{R}_7)$ ; wherein n ranges from 1 to 5; L is O or  $(\text{C}(\text{R}_8)_2)_m$ ; m ranges from 1 to 4; each of the n  $\text{R}_5$ 's and n  $\text{R}_6$ 's is independently selected from the group consisting of the same or different leaving group and the same or different organofluoro moiety;  $\text{R}_7$  is selected from the group consisting of a leaving group and an organofluoro moiety; and each of the  $2n*m$  or fewer  $\text{R}_8$ 's is selected from the group
- 15           consisting of F and the same or different organofluoro moiety.

40. (Cancelled)

41. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said oxidizing agent comprises hydrogen peroxide.

42. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $\text{R}_1$  comprises hydrogen.

43. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_2$  comprises an organofluoro moiety containing  $CF_3$ .
44. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_2$  consists essentially of C and F atoms.
45. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_2$  consists essentially of C and F atoms alone.
46. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_2$  comprises consists essentially of C and F atoms and  $R_3$  consists essentially of an alkyl.
47. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_3$  contains  $CH_3$  moieties.
48. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_4$  comprises a leaving group.
49. (New) The low dielectric constant fluorine and carbon-doped silicon oxide dielectric material of claim 39 wherein said  $R_4$  comprises hydrogen.